

The crystallization process in Ta2O5 and TiO2-Ta2O5 amorphous films

G. Favaro, M. Bazzan, A. Lemaitre, V. Martinez, N. Shcheblanov, M. Granata, S. Capaccioli

Introduction: Noise Sources in Virgo



Among the various Noise source in the mid-frequency sensitivity region (50-300 Hz) the limiting detection factor is currently the Coating Brownian Noise **(CBN)**

This phenomena originates mainly from the amorphous structure of the coatings materials. Although unavoidable the search for materials with lower losses it's fundamental

The solution we investigate to reduce the CBN consist in creating a crystallites dispersion in the materials while avoiding to have too high optical losses



Controlled Crystallization: Experiment





The sample we want to study gets annealed inside our X-Ray facility while being measured at the same time

Only one diffraction peak gets measured during the annealing process to reduce dead time. A full GIXRD spectra of our sample gets acquired at the end of the process

By performing GIXRD experiment we can extract informations regarding the amount of crystallized material and the mean dimension of the crystal grain



Controlled Crystallization: Data

- Ta2O5 is a material with many polymorphs
- The first step is to determine what is the correct structure
- Rietveld analysis on full-profile XRD spectra





In general, we observe the sum of the amorphous spectrum and of the crystallized fraction

Comparison with literature







Structure of Amorphous Tantalum Oxide and Titania-Doped Tantala: ¹⁷O NMR Results for Sol Gel and Ion-Beam-Sputtered Materials, Namjun Kim* and Jonathan F. Stebbins Experimental XRD spectra are well reproducible and coherent with literature. However:

- Disagreement on the type of structure to be attributed
- The most widely accepted structure (β – Ta2O5 orthorhombic) has a very large unit cell with many degree of freedom which makes the results not very significant.



¹⁷O Solid-State NMR Studies of Ta2O5

Nanorods, *Meng Xu*, *Junchao Chen*, *Yujie Wen*, *Jia-Huan Du*, *Zhiye Lin*, *and Luming Peng*



Spectra comparison





The spectra at different temperatures are consistent \rightarrow single phase appearing. Difference related to small changes in structure/microstructure

TiO2:Ta2O5, isochronal annealing up to 900 °C

TiO2:Ta2O5, @ 720 °C, 30h

TiO2:Ta2O5, @ 700 °C, 33h

TiO2:Ta2O5, @ 690 °C, 33h

TiO2:Ta2O5, @ 680 °C, 36h

Ta2O5, @ 680, 33h



Phase Diagram: possible TiO2 - Ta2O5 demixing at high T



FIGURE 1. Phase equilibrium diagram for the system TiO₂-Ta₂O₅.

In all cases, the formation of pure Ta2O5 crystals implies that a demixing process takes place

At T>720°C, extra XRD peaks may point to the formation of TiO2 nanocrystals, i.e., three-phase deximing

Ta2O5 candidate structures





Crystal structures of (a) β -Ta2O5, (b) δ -Ta2O5, (c) the 11 f.u. model, and (d) amorphous tantalum pentoxide.

J. Lee; W. Lu; E. Kioupakis; *Appl. Phys. Lett.* **105,** 202108 (2014) DOI: 10.1063/1.4901939



New structure, derived from recent total scattering data (

- Symmetry: hexagonal
- Space group: P6/mmm
- Cell parameters: a = 7.19 Å; c = 3.83 Å
- VIR-0324A-21
- A. Martinelli et al Phys. Rev. Materials 5, 115603 2021



Rietveld refinement with the hexagonal model



Ta2O5 (s18118)



TiO2:Ta2O5 Microstructure vs annealing temperature



Isotropic model (spherical crystallites)

Temperature	a (Å)	c (Å)	<r> (nm)</r>	microstrain	B _{lso} (Å ²)	Rwp
680°C	7.2106 ± 0.0008	3.8910 ± 0.0006	84 ± 3	$(6.7 \pm 0.4) \times 10^{-4}$	4.5 ± 0.1	14.7%
690°C	7.2135 ± 0.0004	3.8905 ± 0.0004	74 ± 2	$(7.4 \pm 0.1) \times 10^{-4}$	4.6 ± 0.1	18.7%
700°C	7.2139 ± 0.0008	3.8901 ± 0.0006	70 ± 1	$(7 \pm 2) \times 10^{-4}$	4.5 ± 0.1	19.6%
720°C	7.2181 ± 0.0008	3.8895 ± 0.0006	69 ± 3	$(9 \pm 2) \times 10^{-4}$	4.5 ± 0.1	18.4%
lsochronal annealing up to 900°C	7.239 ± 0.001	3.8900 ± 0.0008	64 ± 3	(31 ± 1) ×10 ⁻⁴	4.4 ± 0.1	18.8%







Increasing the annealing temperature both structural and microstructural parameters exhibit a clear trend.

Possible indication that the crystal structures forming at different temperatures are characterized by a different defect structure.



Annealing time = 10h



Crystallization can be detected also by Raman spectroscopy









After an annealing in air at 500°C during 10h



Ab initio Raman simulations : crystal vs amorphous





Raman HH (Pmmm vs amo.)



Raman ISO (Pmmm+P6/mmm vs amo.)



$\underline{\mathbf{Q}}$: one or two cryst. phases are present ?



Crystallization kinetics

(((0)))

Avrami equation describes the evolution of the crystal fraction with respect to time

$$\chi(t) = 1 - exp\left[-\left(\frac{t}{\tau_c}\right)^{\alpha}\right]$$



There are two processes that contribute to crystallization: nucleation and crystal growth. These processes are related to the crystallization time by the formula

$$\tau_c = \left(\frac{\alpha \Gamma(\frac{\alpha+1}{2})}{\pi^{\frac{\alpha-1}{2}} j_{ss} v_g^{\alpha-1}}\right)^{1/\alpha}$$

 α is a characteristic exponent related to the dimensionality of the growth process. For 3D growth α =4.

 J_{SS} : Nucleation rate v_g : Growth velocity



Classical nucleation theory



Nucleation and growth are thermally activated processes. By measuring the energies we are able to compute the effects of an annealing treatment, in terms of average particle size and average density.

$$v_g = \frac{V_0}{k_B T} e^{-\left(\frac{E_f + E_m}{k_B T}\right)}$$

$$j_{ss} = \frac{J_0}{\sqrt{k_B T}} e^{-\left(\frac{E_f + E_m + \Delta G^*}{k_B T}\right)}$$

$$\tau_c^{\alpha} = \frac{\alpha \Gamma\left(\frac{\alpha+1}{2}\right) \left(K_b T\right)^{\frac{2\alpha-1}{2}}}{\pi^{\frac{\alpha-1}{2}} J_0 V_0^{\alpha-1}} e^{-\left(\frac{\alpha E_f + \alpha E_m + \Delta G^*}{K_b T}\right)}$$



Growth velocity





Temperature (°C)	v _g (nm/min)	<r> (nm)</r>
637	0.16 ± 0.02	106 ± 8
644	0.4 ± 0.1	78 ± 5
651	0.6 ± 0.2	93 ± 6
659	0.9 ± 0.2	114 ± 5
680	2.4 ± 0.7	86 ± 3



Temperature (°C)	v _g (nm/min)	<r> (nm)</r>
680	0.32 ± 0.04	80 ± 40
690	0.61 ± 0.06	80 ± 30
700	1.4 ± 0.4	80 ± 30
720	5 ± 1	80 ± 10

- At equal temperatures, Ti-doped tantala displays a much slower growth rates.
- Possibly, Ti atoms form bonds that hinder Ta and O atoms rearrangement

The observed decrease in particle size for the TiO2 - Ta2O5 is probably an artifact due to the slow buildup of microstrain during the annealing process

Activation energies





Ta2O5 : Ef + Em = (4.5 ± 0.6) eV TiO2 - Ta2O5 : Ef + Em = (5.5 ± 0.3) eV

The addition of TiO2 slows down the crystal growth process and seems to increase the activation energy required to rearrange the atoms at the grain surface.



Crystallization Kinetics





Avrami equation in double-log anamorphosis:

$$ln\left[-ln\left(1-\chi(t)\right)\right] = \alpha ln(t) + q$$

Evidence for 3D growth



Crystallization characteristic time in Ta2O5

$$\ln\left[\tau_c^4 \left(K_b T\right)^{-\frac{7}{2}}\right] = \ln\left[\frac{4\Gamma\left(\frac{5}{2}\right)}{\pi^{\frac{3}{2}}J_0 V_0^3}\right] - \left(\frac{4E_f + 4E_m + \Delta G^*}{K_b T}\right)$$
$$\ln\left[\tau_c^4 \left(K_b T\right)^{-\frac{7}{2}}\right] = a - \left(\frac{Q}{K_b T}\right)$$





- Old Model:
 - $Q = (-15.0 \pm 0.6) eV$
 - a = 0 ± 10
- New Model:
 - Q = (-20 ± 2) eV
 - a = -60 ± 30

Conclusions



What have we learned?

- XRD suggest that Ta2O5 crystallizes into a P6/mmm phase.
- Crystallization signatures are present in Raman as well.
- Comparison between different samples and with ab initio data suggest that post-annealed samples always contain a mixture of amorphous and crystallized volume
- The microstructure of the crystalline grains have been investigated by means of Rietveld analysis. Higher temperatures produce different amount of defects.
- The crystallization kinetics have been characterized. It proceeds by nucleation and 3D growth of spherical nanoparticles in a typical size of 50-100 nm. The activation energy of the growth process is about 5 eV. The addition of titania (at 21%) to the mixture slows down the growth velocity of about one order of magnitude.

What is still missing?

- Evidence demixing of TiO2 at higher T?
- Combine with TEM analysis to check the microstructure
- Optical scattering analysis
- Loss angle measurements



Thank You For your Attention

